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Pre-Amend #8

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: SHIMOYAMA et al.

PATENT APPLICATION

Serial Number: (Divisional of Appln. Serial No.
08/970,145, filed November 13, 1997

Prior Art Unit: 2814

Filed: Herewith

6,265,133

Prior Examiner: D. Wille

For: SEMICONDUCTOR DEVICE, SEMICONDUCTOR DEVICE AND METHOD
FOR MANUFACTURING THE SAME

PRELIMINARY AMENDMENT

Director of Patents and Trademarks
Washington, D.C. 20231

Date: February 20, 2001

Sir:

Prior to examination, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 1-27 without prejudice or disclaimer and add new claims 28-54 as follows:

--28. A light emitting semiconductor device comprising a semiconductor substrate, a first conductivity type epitaxial layer and a second conductivity type epitaxial layer or a high resistance epitaxial layer stacked one upon another, a V-groove having a V-shaped cross-section on the semiconductor, wherein an inclined surface of said V-groove is formed from the first conductivity type epitaxial layer to the second conductivity type epitaxial layer or the high resistance epitaxial layer, a bottom of the V-groove lies in said first conductivity type epitaxial layer, a side wall of the V-groove is in contact with the second conductivity type epitaxial layer or the high resistance

00220-8293260

AI
Wille